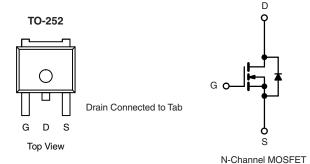


www.vishay.com

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.009			
I _D (A)	50			
Configuration	Single			



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified^d
- Compliant to RoHS Directive 2002/95/EC



FREE

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50N04-09H-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40	.,	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C ^a	- I _D -	50		
	T _C = 125 °C		40		
Continuous Source Current (Diode Conduction) ^a		I _S	50	Α	
Pulsed Drain Current ^b		I _{DM}	200		
Single Pulse Avalanche Energy	L = 0.1 mH	I _{AS}	39		
Single Pulse Avalanche Current	L = 0.1 min	E _{AS}	76	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	- P _D	83	W	
	T _C = 125 °C		27	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.8		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							,
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		3.8	5.0	\ \
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		=	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 40 V	=	-	1.0	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	=.	-	250	1
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 20 A	=	0.0068	0.0090	Ω
	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.015	
		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	=.	-	0.018	
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		=.	48	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			=	3390	4240	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}$ $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	=	408	510	pF	
Reverse Transfer Capacitance	C _{rss}			=	164	205	1
Total Gate Charge ^c	Qg		= 10 V V _{DS} = 20 V, I _D = 50 A	=.	51	76	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V		=	19.4	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		=.	8.5	-	
Gate Resistance	R _g	f = 1 MHz		0.65	1.3	2	Ω
Turn-On Delay Time ^c	t _{d(on)}			=.	15	23	
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 0.4 \Omega$ $I_{D} \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		=.	14	21	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	23	35	
Fall Time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Char-	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	200	Α
Forward Voltage	V _{SD}	I _F = 30 A, V _{GS} = 0 V		-	0.9	1.5	V

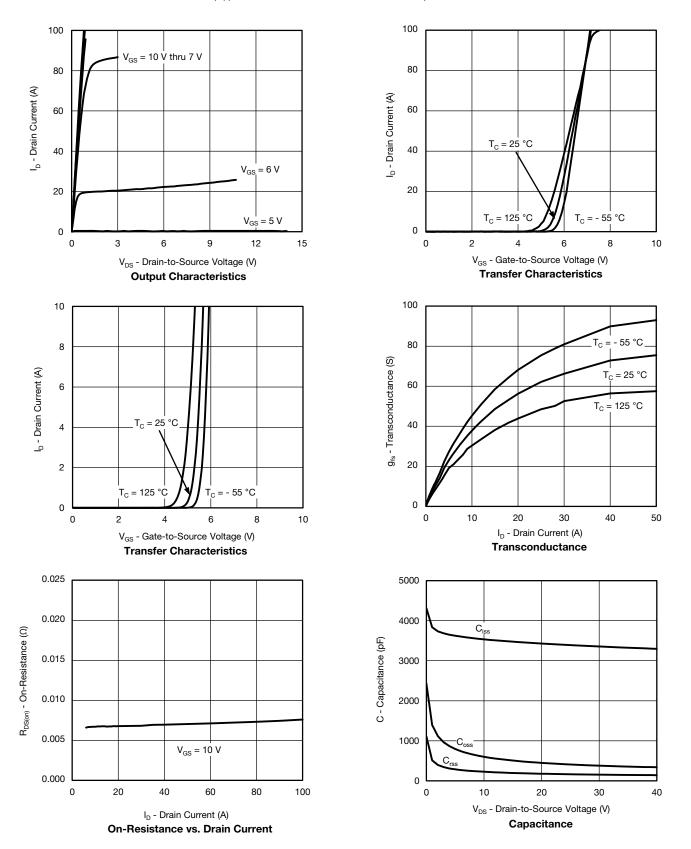
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

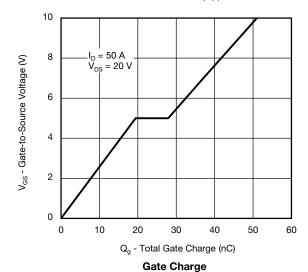


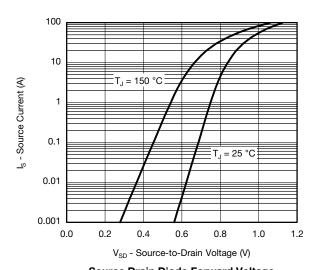
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

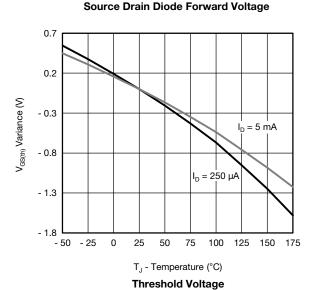


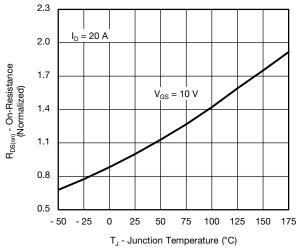


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

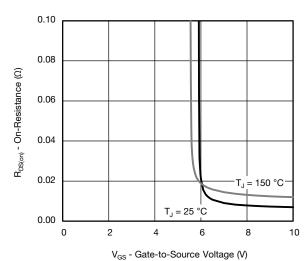




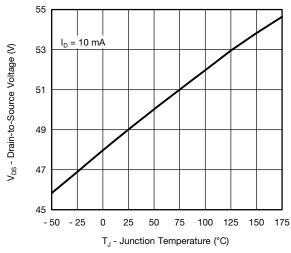








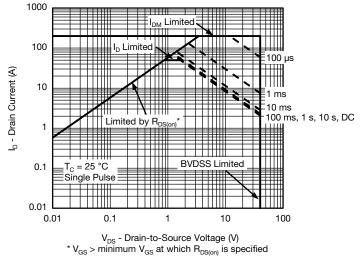
On-Resistance vs. Gate-to-Source Voltage



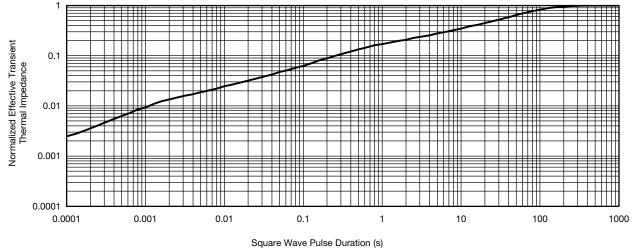
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



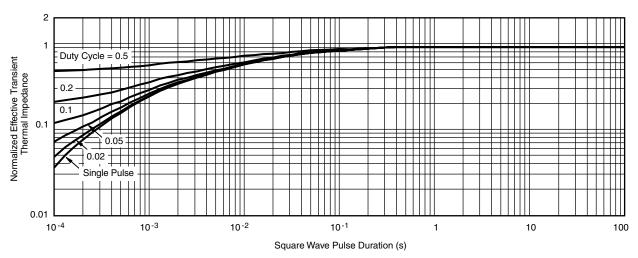
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 $^{\circ}\text{C})$

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg264702.



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